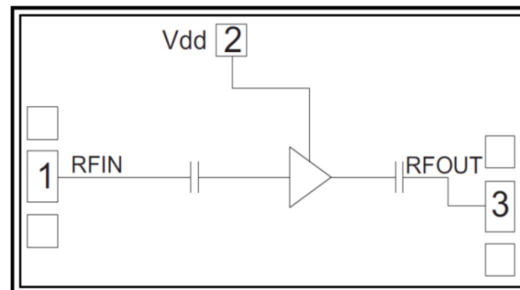
GaAs MMIC
Low Noise Amplifier
2-4GHz

Features

- Frequency: 2-4GHz
- Small Signal Gain: 29dB
- Noise Figure: 0.6dB max.
- P1dB: 7dBm
- Power Supply: +5V/15mA
- Input/Output: 50Ω
- Die Size: 1.85 x 1.25 x 0.1 mm

Functional Block Diagram



Typical Applications

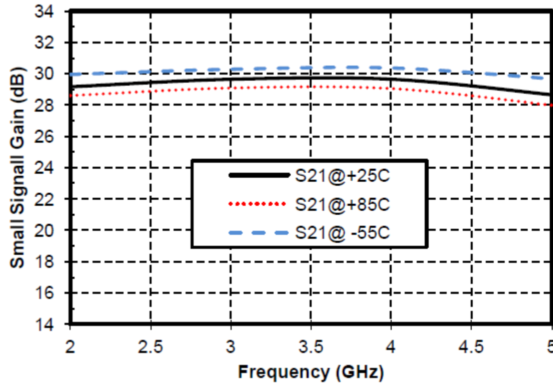
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

Electrical Specifications

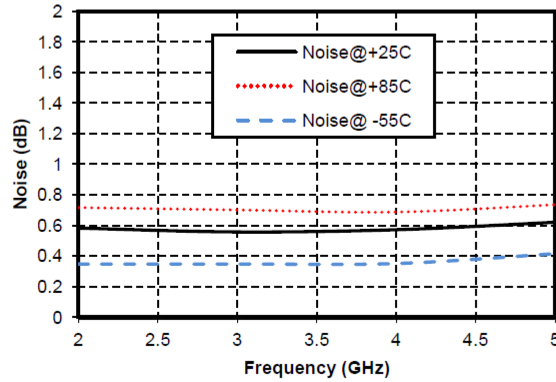
TA = +25ºC, Vd = +5V

Parameters	Min.	Typ.	Max.	Units
Frequency		2-4		GHz
Small Signal Gain		29		dB
Gain Flatness		±0.25		dB
Noise Figure			0.6	dB
Output 1dB Compression (P1dB)	6.5	7	7.5	dBm
Saturated Output Power (Psat)	8	8.5	9	dBm
Input Return Loss	10	14	-	dB
Output Return Loss	18	24	-	dB
Static current		15		mA

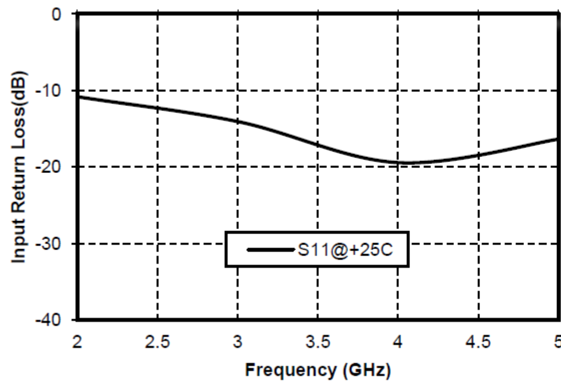
Gain vs. Frequency



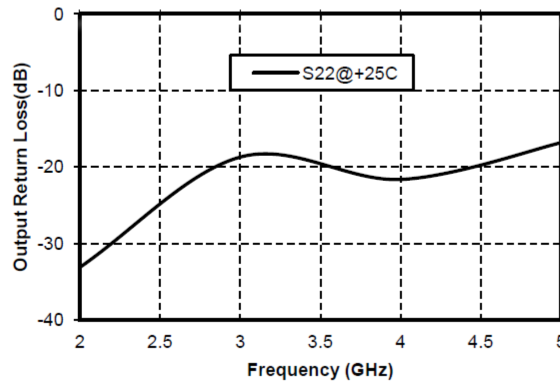
Noise Figure vs. Frequency



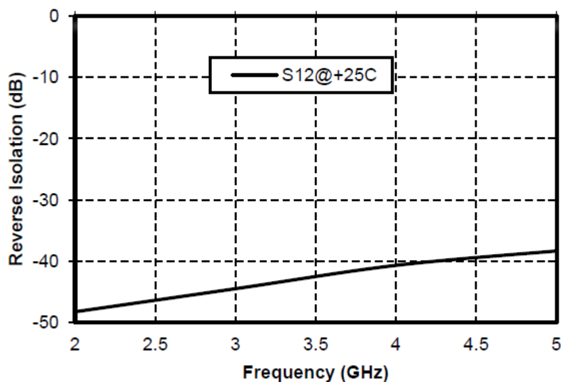
Input Return Loss vs. Frequency



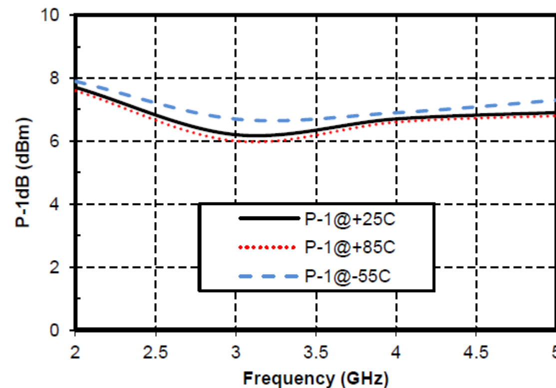
Output Return Loss vs. Frequency



Reverse Isolation vs. Frequency

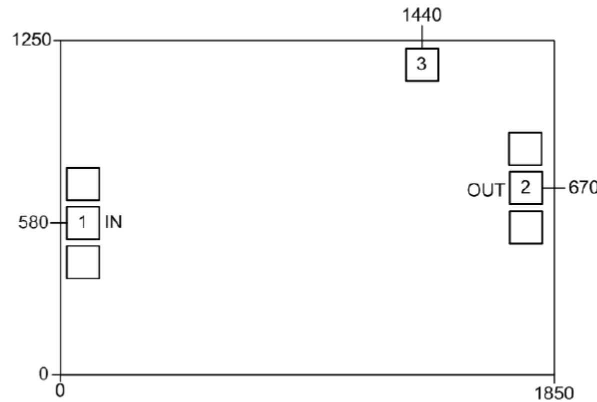


P1dB vs. Frequency



Outline Drawing:

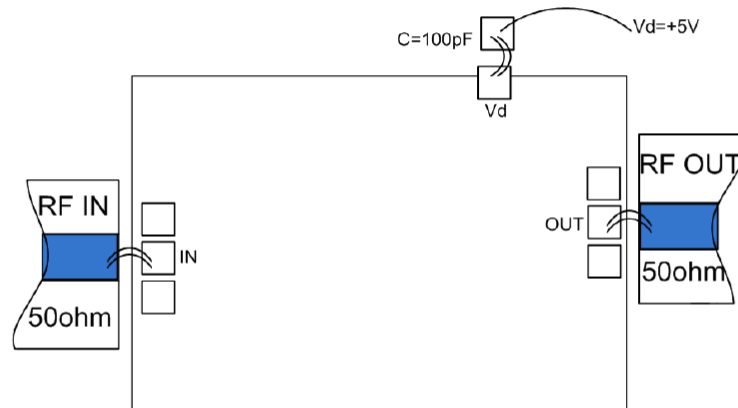
All Dimensions in µm



Pad Description

Pad	Function	Description	Equivalent Circuit
1	RF IN	RF signal input terminal, no blocking capacitor required.	RF IN
2	RF OUT	RF signal output terminal, no blocking capacitor required.	RF OUT
3	Vd	Amplifier drain bias; external 100pF bypass capacitor required.	Vdd
Die bottom	GND	Die bottom must be connected to RF/DC ground.	GND

Assembly Drawing



Notes:
1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:
1. Maximum drain voltage: +7V
2. Maximum input power: +20dBm
3. Operating temperature: -55℃ to +85℃
4. Storage temperature: -65℃ to +150℃